Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1-9 (Canceled)

Claim 10 (Previously Presented): A method of depositing a wiring thin film over a semiconductor substrate, the method comprising:

providing a Al_3Ti target;

providing a substrate;

forming a Ti layer over said substrate;

sputter depositing an Al_3Ti layer on said Ti layer using said Al_3Ti target; and,

after the sputter depositing, annealing said substrate at a temperature of at least 400°C to promote absorption of Si into said Al_3Ti layer.

Claim 11 (Previously Presented): A method as recited in claim 10, wherein an Al layer is deposited on said Al_3Ti layer.

Claim 12 (Previously Presented): A method as recited in claim 10, further comprising pattern-etching said Al layer thereby forming a wiring pattern.

Claim 13 (Previously Presented): A method as recited in claim 10, wherein the method further comprises forming an insulating layer between said substrate and said Al_3Ti layer.

Claim 14 (Currently Amended): A method of forming a wiring film, the method comprising:

providing a substrate;

depositing a Ti layer over said substrate;

depositing an Al-Si-Cu layer on said Ti layer[[,]] ~~which forms an Al_3Ti on said Ti layer~~;

pattern etching an Al layer, which forms beneath said Al-Si-Cu layer; and

after the depositing of the Al-Si-Cu layer, annealing the substrate at a temperature of at least 400°C to form an Al_3Ti layer on said Ti layer.

Claims 15-16 (Canceled)

Claim 17 (Previously Presented): A method of forming a wiring film, the method comprising:

providing a substrate;

depositing an Al_3Ti layer over said substrate;

depositing an Al layer on said Al_3Ti layer;

pattern etching said Al layer; and

after the depositing of the Al layer, annealing the substrate at a temperature of at least 400°C.

Claim 18 (Previously Presented): A method as recited in claim 17, wherein said Al layer is deposited at a temperature of at least 400°C.

19. (Cancelled)

Claim 20 (Previously Presented): A method as recited in claim 17, wherein said Al_3Ti layer is deposited at a temperature of at least 400°C.